

BD034
Rev.E Mar.-2016

KF \$() - = GE G Silicon PNP transistor in a

BD034

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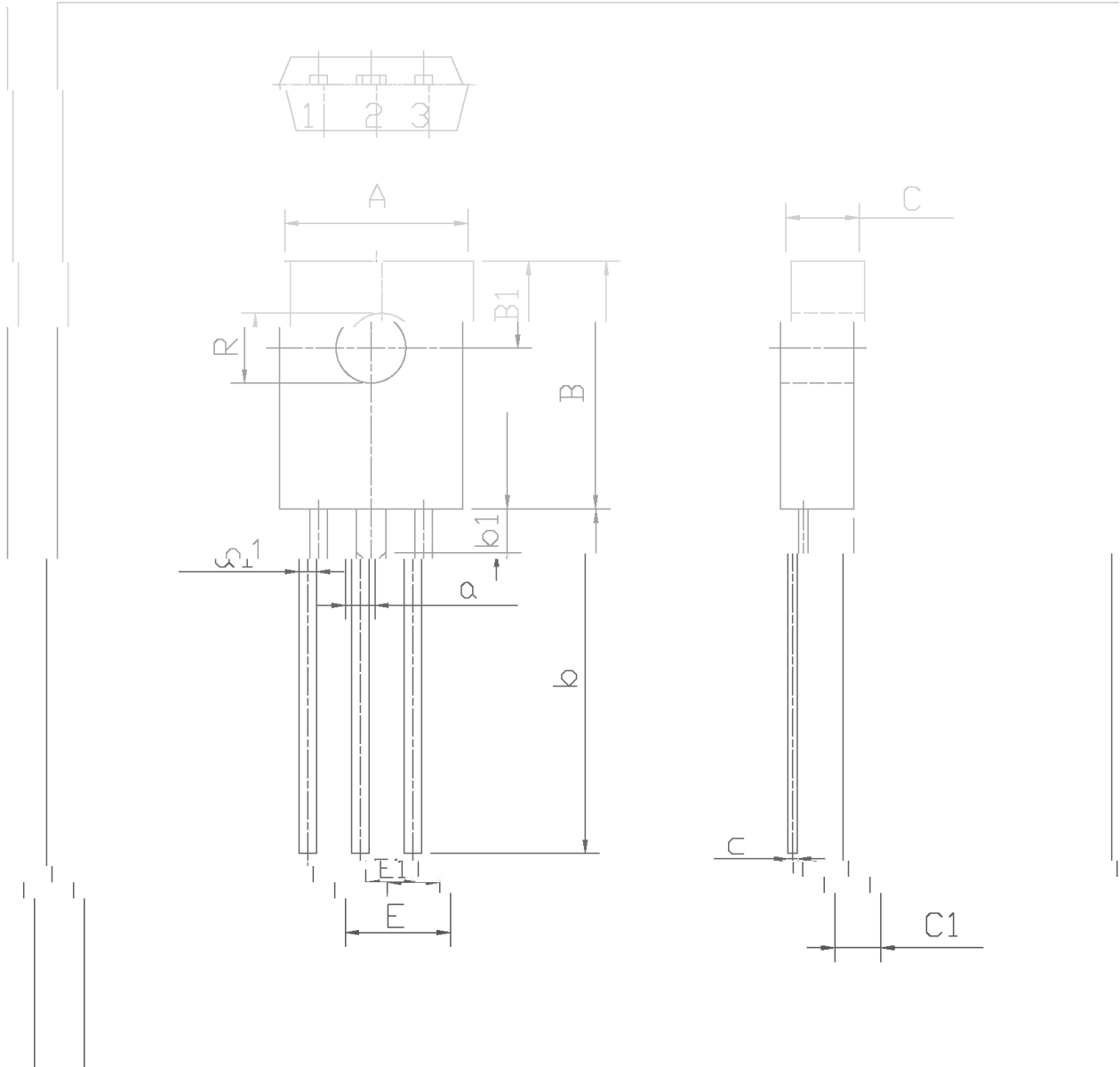
| Parameter | Symbol | Rating | Unit |
|--------------------------------|-----------|---------|------|
| Collector to Base Voltage | V_{CBO} | -110 | V |
| Collector to Emitter Voltage | V_{CEO} | -80 | V |
| Emitter to Base Voltage | V_{EBO} | -7.0 | V |
| Collector Current - Continuous | I_C | -2.5 | A |
| Collector Power Dissipation | P_C | 1.25 | W |
| Junction Temperature | T_j | 150 | °C |
| Storage Temperature Range | T_{stg} | -55 150 | °C |

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-----------------------------------------------------------------------|-----------|---------------------------------|------|-----|-----|------|
| Collector to Base Breakdown Voltage Collector to Emitter Breakdown | V_{CBO} | $I_C = -100\text{ A}$ $I_B = 0$ | -110 | | | V |

/ Package Dimensions

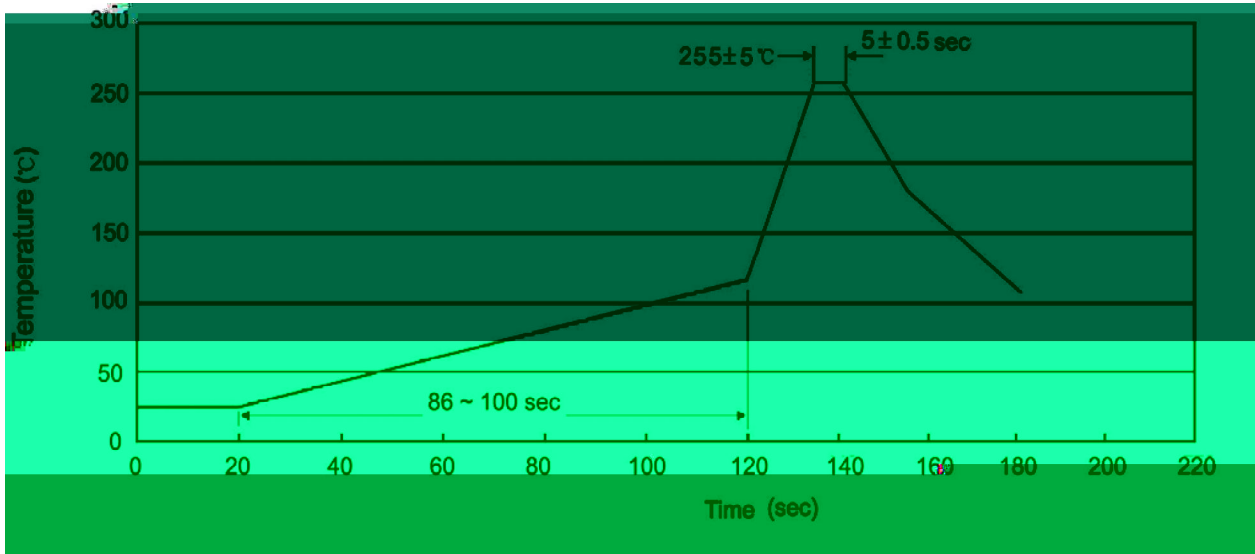
1 2 3

单位: mm



| Symbol | Dimension in Millimeters | | Symbol | Dimension in Millimeters | |
|--------|--------------------------|------|--------|--------------------------|------|
| | Min | Max | | Min | Max |
| A | 7.8 | 8.2 | a1 | 0.66 | 0.86 |
| B | 10.8 | 11.2 | E | 4.4 | 4.8 |
| B1 | 3.8 | 4.2 | C | 3.1 | 3.3 |
| R | 2.05 | 2.15 | c1 | 1.9 | 2.1 |
| b | 14 | 16 | c | 0.3 | 0.6 |
| b1 | | 1.9 | a | | 1.27 |
| E1 | 2.1 | 2.5 | | | |

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | |
|---|--------|------------|-------------------------------------------|
| 1 | 25 150 | 60 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | 5..0.5sec; | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | 2 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270..5 10..1 sec. Temp.:270±5°C Time:10±1 sec

/ Packaging SPEC.

/ BULK

| Package Type 封装形式 | Units 包装数量 | Dimension 包装尺寸 (unit: mm ³) |
|----------------------|------------|-----------------------------------------|
| 只 套管 套管 盒 | 只 盒 | |